

**ADVANCED
POWER
TECHNOLOGY®**

APT601R3GN	600V	5.5A	1.30Ω
APT551R3GN	550V	5.5A	1.30Ω
APT601R6GN	600V	5.0A	1.60Ω
APT551R6GN	550V	5.0A	1.60Ω

POWER MOS IV™

N - CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT 551R3GN	APT 601R3GN	APT 551R6GN	APT 601R6GN	UNIT
V _{DSS}	Drain-Source Voltage	550	600	550	600	Volts
I _D	Continuous Drain Current @ T _C = 25°C	5.5		5.0		Amps
I _{DM}	Pulsed Drain Current ①	22		20		
V _{GS}	Gate-Source Voltage	±30				Volts
P _D	Total Power Dissipation @ T _C = 25°C	100				Watts
	Linear Derating Factor	0.8				W/°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150				°C
T _L	Lead Temperature: 0.063" from Case for 10 Sec.	300				

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu A$)	APT601R3GN / APT601R6GN	600			Volts
		APT551R3GN / APT551R6GN	550			
$I_{D(ON)}$	On State Drain Current ② ($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)	APT601R3GN / APT551R3GN	5.5			Amps
		APT601R6GN / APT551R6GN	5.0			
$R_{DS(ON)}$	Drain-Source On-State Resistance ② ($V_{GS} = 10V, 0.5 I_D$ [Cont.])	APT601R3GN / APT551R3GN			1.30	Ohms
		APT601R6GN / APT551R6GN			1.60	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)				250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)				1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)				± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1.0mA$)		2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			1.20	°C/W
$R_{\theta JA}$	Junction to Ambient			80	

405 S.W. COLUMBIA STREET
BEND, OREGON 97702-1035
U.S.A.

PHONE . . . (503) 382-8028

FAX (503) 388-0364

DYNAMIC CHARACTERISTICS

APT61R3/551R3/601R6/551R6GN

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{DC}	Drain-to-Case Capacitance	$f = 1 \text{ MHz}$		8	12	pF
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		764	950	
C_{oss}	Output Capacitance			153	214	
C_{rss}	Reverse Transfer Capacitance			54	81	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		34	55	nC
Q_{gs}	Gate-Source Charge			4.6	7	
Q_{gd}	Gate-Drain ("Miller") Charge			15	23	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 1.8\Omega$		10	20	ns
t_r	Rise Time			15	30	
$t_d(\text{off})$	Turn-off Delay Time			36	54	
t_f	Fall Time			13	26	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT601R3GN / APT551R3GN		5.5	Amps
		APT601R6GN / APT551R6GN		5.0	
I_{SM}	Pulsed Source Current ① (Body Diode)	APT601R3GN / APT551R3GN		22	
		APT601R6GN / APT551R6GN		20	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V$, $I_S = -I_D [\text{Cont.}]$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)	130	260	520	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)	1.3	2.6	5.2	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}$, $I_{DS} = P_D / 0.4 V_{DSS}$, $t = 1 \text{ Sec.}$	100			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}]$, $V_{DS} = P_D / I_D [\text{Cont.}]$, $t = 1 \text{ Sec.}$	100			
I_{LM}	Inductive Current Clamped	APT601R3GN / APT551R3GN	22			Amps
		APT601R6GN / APT551R6GN	20			

① Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

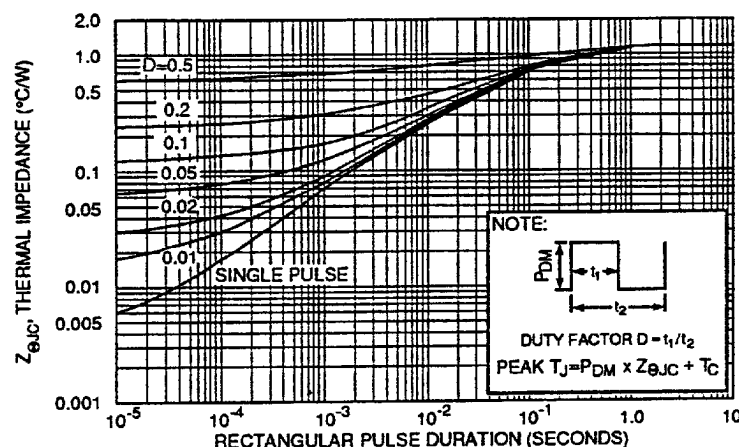


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

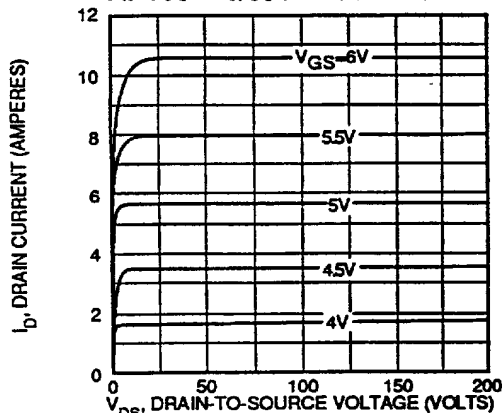


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

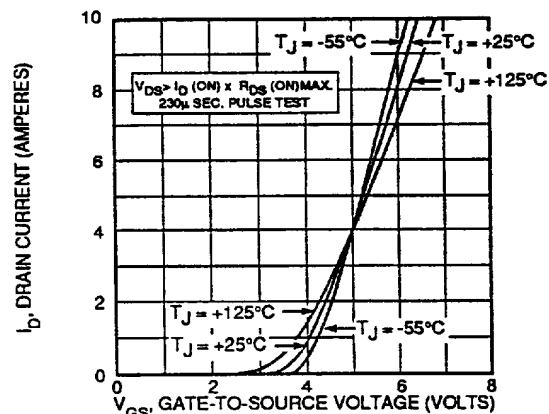


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

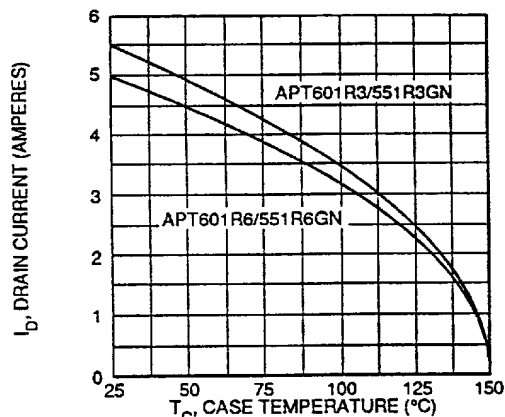


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

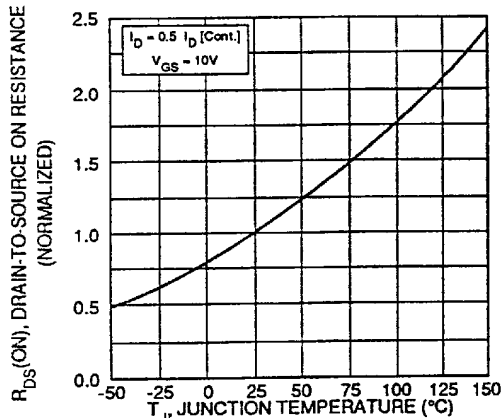


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

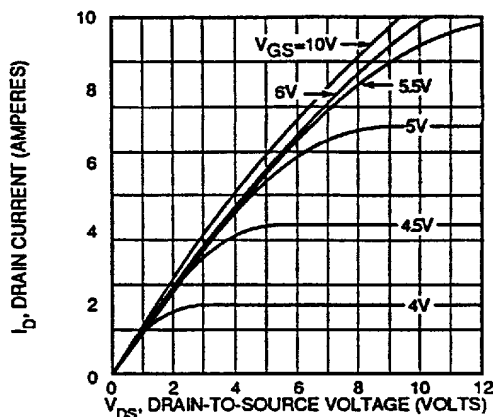


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

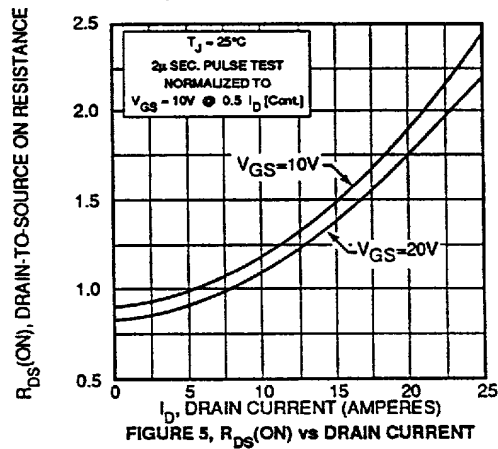


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

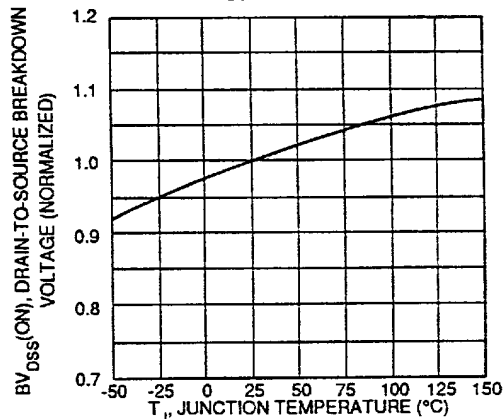


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

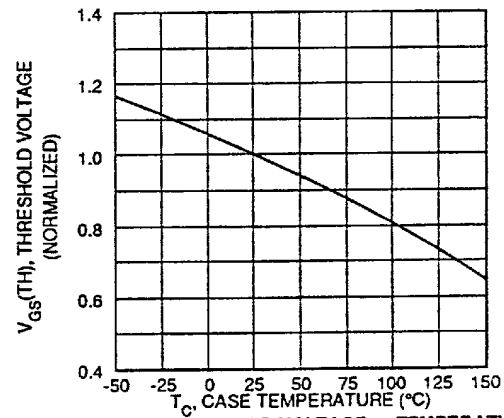


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

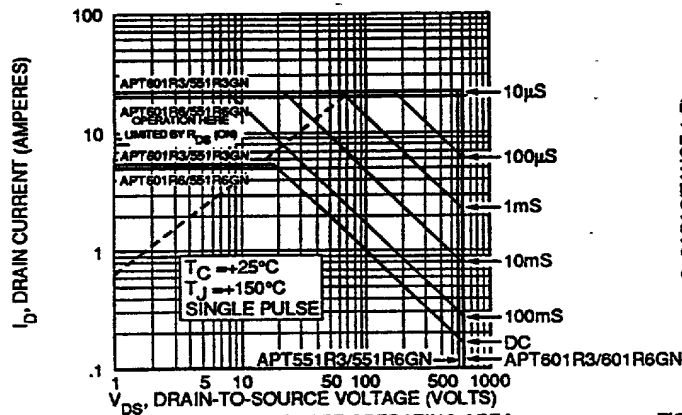


FIGURE 10, MAXIMUM SAFE OPERATING AREA

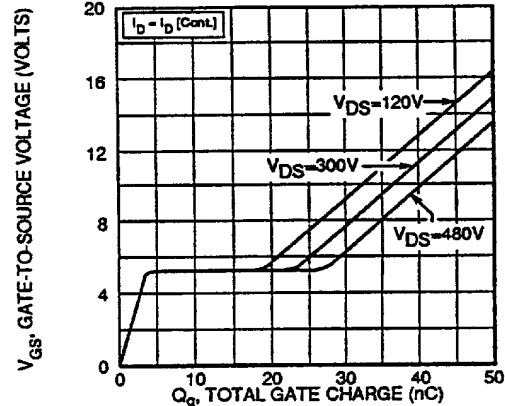


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

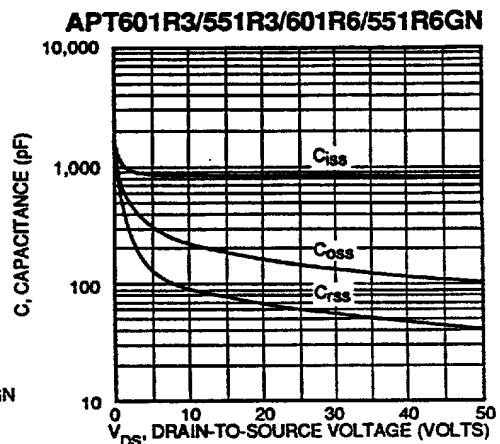


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

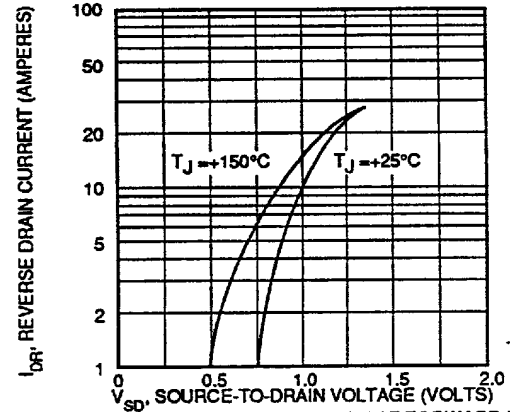
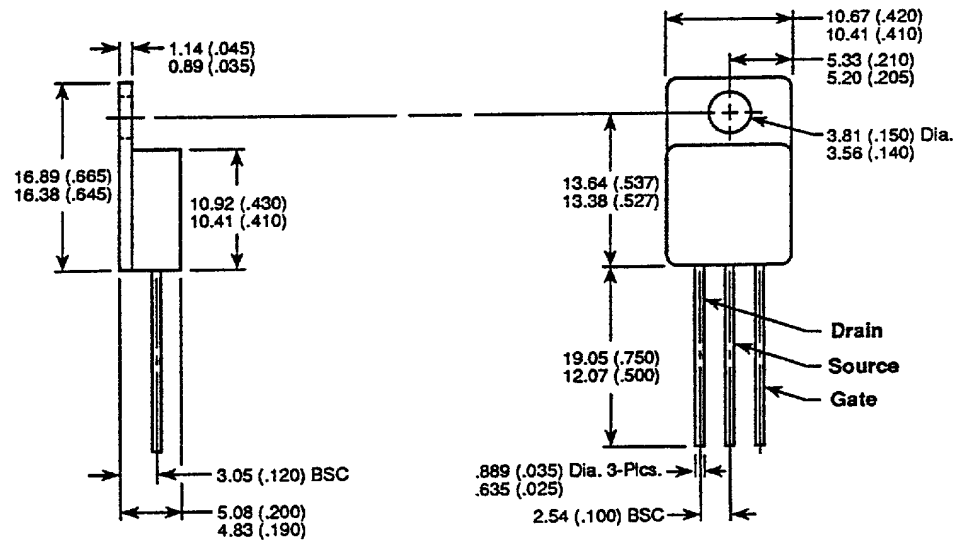


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-257AA Package Outline



Dimensions in Millimeters and (Inches)